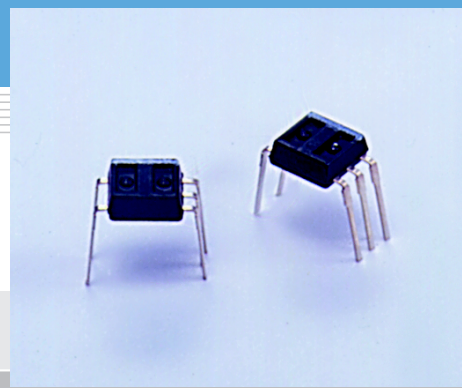


Photoreflector

P4855, P4856

Photo IC output (digital) photoreflectors



P4855 and P4856 are photoreflectors combining a high power infrared LED and a single chip photo IC consisting of a high sensitivity photodiode, amplifier, schmitt trigger circuit, and output phototransistor, etc.

Features

- Miniature package
- Photo IC, open collector output
- P4855: "H" level output at light input
P4856: "L" level output at light input

Applications

- Paper detection in copiers and printers, etc.
- Tape end detection in VTRs, tape recorders, etc.

■ Absolute maximum ratings (Ta=25 °C)

Parameter		Symbol	Value	Unit
Input (LED)	Forward current	IF	50	mA
	Reverse voltage	VR Max.	5	V
	Power dissipation	P	80	mW
Output (photo IC)	Supply voltage	Vcc	-0.5 to +12	V
	Output voltage	Vo	-0.5 to +12	V
	Low level output current	Io	50	mA
	Power dissipation	P	150	mW
Operating temperature		Topr	-25 to +85	°C
Storage temperature		Tstg	-30 to +85	°C
Soldering		-	260 °C, 3 s, refer to Dimensional outline	-

■ Electrical and optical characteristics (Ta=25 °C, Vcc=5 V, unless otherwise noted)

Parameter		Symbol	Condition	P4855			P4856			Unit
				Min.	Typ.	Max.	Min.	Typ.	Max.	
Input (LED)	Forward voltage	VF	IF=20 mA	-	1.3	1.6	-	1.3	1.6	V
	Reverse current	IR	VR=5 V	-	-	10	-	-	10	μA
	Terminal capacitance	Ct	V=0 V, f=1 MHz	-	30	-	-	30	-	pF
Output (photo IC)	Operating supply voltage	Vcc		4.5	-	12	4.5	-	12	V
	Low level output voltage	VOL	IoL=16 mA *1	-	0.1	0.4	-	0.1	0.4	V
	High level output current	IOH	Vo=5 V *2	-	-	100	-	-	100	μA
	Current consumption at low level output	ICCL	*1	-	3.5	12	-	3.5	12	mA
	Current consumption at high level output	ICCH	*2	-	1.8	10	-	2.3	10	mA
Transfer characteristics	L→H Threshold illuminance	IFLH	RL=280 Ω, d=3 mm Reflecting surface: white paper (reflectivity 90 % or more)	-	-	15	-	-	-	mA
	H→L Threshold illuminance	IFHL		-	-	-	-	-	15	mA
	Hysteresis	-	*3	-	0.9	-	-	0.9	-	-
	L→H Propagation delay time	tPLH		-	-	9	-	-	15	μs
	H→L Propagation delay time	tPHL	IF=20 mA	-	-	15	-	-	9	μs
	Rise time	tr	RL=280 Ω	-	0.15	-	-	0.15	-	μs
	Fall time	tf	d=3 mm	-	0.03	-	-	0.03	-	μs

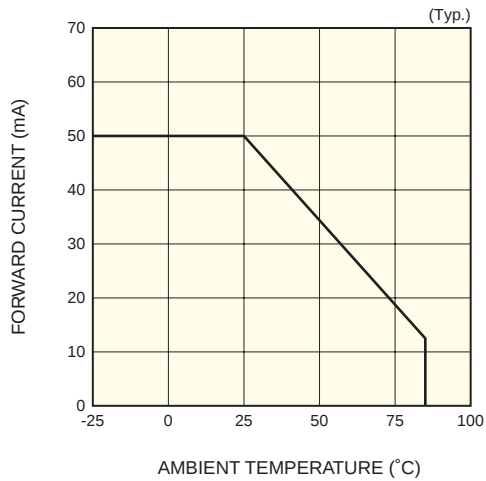
*1: P4855: IF=0 mA, P4856: IF=20 mA

*2: P4855: IF=20 mA, P4856: IF=0 mA

*3: P4855: IFHL/IFLH, P4856: IFLH/IFHL

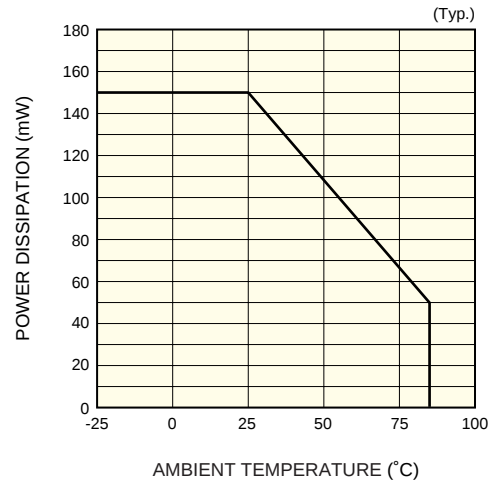
Note) Connect a 0.01 μF capacitor or larger between Vcc and GND.

LED forward current vs. ambient temperature



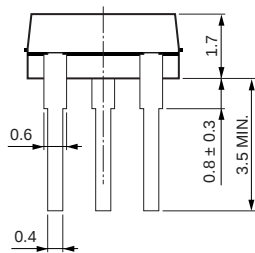
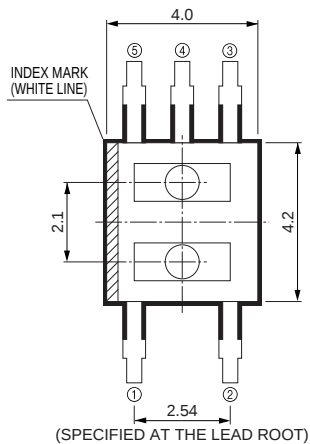
KLEDB0081EA

Photo IC power dissipation vs. ambient temperature



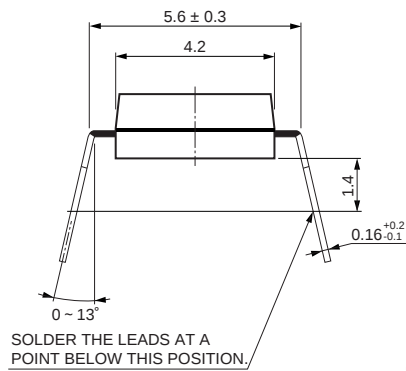
KPICB0023EA

Dimensional outline (unit: mm)

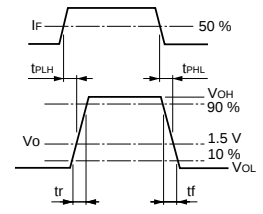
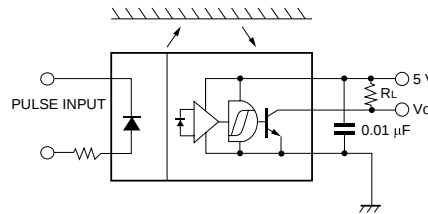


① CATHODE
② ANODE
③ V_O
④ GND
⑤ V_{CC}

Tolerance unless otherwise noted: ±0.2
Shaded area indicates burr.



KPCA0002EA



KPCC0001EA

HAMAMATSU

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